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IPA		10/690,02	029					
RANSI	Filing Date	October 2	per 20, 2003					
on S FOF	First Named Inventor	Garo J. De	Garo J. Derderian					
7 2 8 2004 2	Art Unit	2812	2812					
(to be uses) or all correspo	ondence after initial filing)	Examiner Name	Unknown	Unknown				
(to be used or all correspondence of Pages in T	his Submission	Attorney Docket Number	MI22-2426	3				
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This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Reent Application Serial No	10/690,029
Reent Application Serial Noling Date	October 20, 2003
Inventor	Garo J. Derderian
Assignee	Micron Technology, Inc.
Group Art Unit	2812
Examiner	Unknown
Attorney Docket No	Ml22-2426
Customer No	021567
Title: Methods of Forming Conductive Me	etal Silicides by Reaction of Metal with
Silicon	•

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. Pursuant to 1276 OG 55, August 5, 2003, no copies of cited U.S. patents or U.S. patent application publications are included, as the date of filing of this patent application occurs after June 30, 2003. Copies of all other references are attached. No admission is made regarding whether all the listed references are prior art.

Citation of the referenced art is respectfully requested.

This Supplemental Information Disclosure Statement is being filed before the mailing date of a first Office Action. There, no fee is believed to be required. However, in the event that a fee is required for filing this Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 10-28-09

Mark S. Matkin Reg. No. 32,268

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APPLICANT: Garo J. Derderian et al.

FILING DATE October 20, 2003

GROUP 2812

U.S. PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name		Subclass	Filing Date If Appropriate			
	AA	3,349,474	12/1963	D. H. Rauscher						
_	A8	5,904,517	05/1999	Gardner et al.	438	197		•		
	AC	5,998,264	12/1999	Wu	438	260				
	AD	6,180,465 B1	01/2001	Gardner et al.	438	291				
	AE	6,207,485 B1	03/2001	Gardner et al.	438	216				
	AF	6,548,854 B1	04/2003	Kizilyalli et al.	257	310				
	AG							-		
	АН	2003/0045060 A1	03/2003	Ahn et al.	438	287				
	Al	2003/0045078 A1	03/2003	Ahn et al.	438	585				
	AX AL	Number EP 0 851 473 A2	01/1998	EPO			Yes X	No		
OTHER RE	Т	CES (including Author,		ertinent Pages, Etc.) treatments in advanced MOS gate process	sing, Micro	pelectronic E	ngineerir	ıg,		
:	АМ	(2004), pages 1	130-135							
	AN		Lemberger et al., Electrical characterization and reliability aspects of zirconium silicate films obtained from novel MOCVD precursors, Microelectronic Engineering (2004), pages 315-320							
	AO	Lu et al., Effect	Lu et al., Effects of the TaN _x interface layer on doped tantalum oxide high-k films, VACUUM (2004), pages 1-9							
EXAMINER DATE CONSIDERED										

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. PATEN	NT DO	CUMENTS								
*Examiner's Initials		Document Number				Class	Subclass		Filing Date If Appropriate	
	AA	10/932,218		Basceri et al.					09/01/2004	
	AB									
	AC									
	AD									
	AE									
	AF									
	AG									
	АН									
	AJ									
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	AL									
OTHER RE	FEREN	NCES (including Author,	Title, Date, Po	ertinent Pages, Etc.)				, ·		
	АМ	Robertson et a Microelectronic	Robertson et al., Atomic structure, band offsets, growth and defects at high-K oxide:Si enterfaces, Microelectronic Engineering (2004) pages 112-120							
										I
	AN	Singh et al., Hi	gh and Low D	Dielectric Constant Material	ls, The Electroch	nemical Sc	ociety II	nterfac	ce, Summ	ier
		1999, pages 26	<u>3-30</u>							
	AO									
				-	-					
EXAMINER	INER DATE CONSIDERED									
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